

MAGNETIC RANDOM ACCESS MEMORY CELL

Abstract of the Disclosure

A memory cell for use in a magnetic random access memory (MRAM) circuit includes at least first and second transistors formed in a semiconductor layer. A first insulating layer is
5 formed on at least a portion of the first and second transistors. The memory cell further includes a first magnetic storage element formed on at least a portion of the first insulating layer, at least a second insulating layer formed on at least a portion of the first magnetic storage element, and at least a second magnetic storage element formed on at least a portion of the second insulating layer. The first and second magnetic storage elements are electrically connected to the first and
10 second transistors, respectively.